Abstracts

A 4GHz Low Noise GaAsFET Amplifier

L. Hao-mo. "A 4GHz Low Noise GaAsFET Amplifier." 1981 MTT-S International Microwave Symposium Digest 81.1 (1981 [MWSYM]): 447-449.

A 4GHz low noise GaAsFET amplifier has been designed and fabricated. Time-delay protection circuit and input circuit without separation DC element has been used. The performence of two stages 4,0-4,5 GHz amplifier is N/sub F/ 2 db, G/sub a/ 24 db.

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